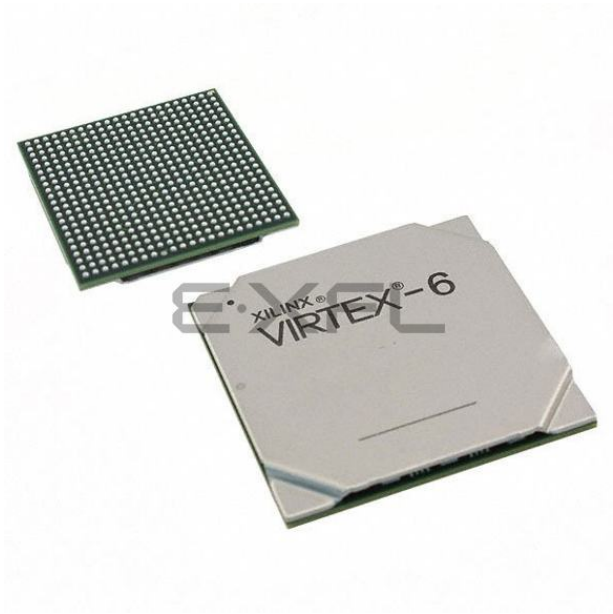
AMD Xilinx - XC6VLX760-2FFG1760C Datasheet



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Details	
Product Status	Active
Number of LABs/CLBs	59280
Number of Logic Elements/Cells	758784
Total RAM Bits	26542080
Number of I/O	1200
Number of Gates	-
Voltage - Supply	0.95V ~ 1.05V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	1760-BBGA, FCBGA
Supplier Device Package	1760-FCBGA (42.5x42.5)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc6vlx760-2ffg1760c

Table 2: **Recommended Operating Conditions**

Symbol	Description	Min	Max	Units
V_{CCINT}	Internal supply voltage relative to GND for all devices except -1L devices.	0.95	1.05	V
	For -1L commercial temperature range devices: internal supply voltage relative to GND, T_j = 0°C to +85°C	0.87	0.93	V
	For -1L industrial temperature range devices: internal supply voltage relative to GND, T_j = –40°C to +100°C	0.91	0.97	V
V_{CCAUX}	Auxiliary supply voltage relative to GND	2.375	2.625	V
V_{CCO}(1)(2)(3)	Supply voltage relative to GND	1.14	2.625	V
V_{IN}	2.5V supply voltage relative to GND	GND – 0.20	2.625	V
	2.5V and below supply voltage relative to GND	GND – 0.20	V_{CCO} + 0.2	V
I_{IN}(5)	Maximum current through any pin in a powered or unpowered bank when forward biasing the clamp diode.	–	10	mA
V_{BATT}(6)	Battery voltage relative to GND	1.0	2.5	V
V_{FS}(7)	External voltage supply for eFUSE programming	2.375	2.625	V
T_j	Junction temperature operating range for commercial (C) temperature devices	0	85	°C
	Junction temperature operating range for extended (E) temperature devices	0	100	°C
	Junction temperature operating range for industrial (I) temperature devices	–40	100	°C
	Junction temperature operating range for military (M) temperature devices	–55	125	°C

Notes:

1. Configuration data is retained even if V_{CCO} drops to 0V.
2. Includes V_{CCO} of 1.2V, 1.5V, 1.8V, and 2.5V.
3. The configuration supply voltage V_{CC_CONFIG} is also known as V_{CCO_0}.
4. All voltages are relative to ground.
5. A total of 100 mA per bank should not be exceeded.
6. V_{BATT} is required only when using bitstream encryption. If battery is not used, connect V_{BATT} to either ground or V_{CCAUX}.
7. During eFUSE programming, V_{FS} must be within the recommended operating range and T_j = +15°C to +85°C. Otherwise, V_{FS} can be connected to GND.

Table 3: **DC Characteristics Over Recommended Operating Conditions (1)(2)**

Symbol	Description	Min	Typ	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost)	0.75	–	–	V
V_{DRI}	Data retention V_{CCAUX} voltage (below which configuration data might be lost)	2.0	–	–	V
I_{REF}	V_{REF} leakage current per pin	–	–	10	µA
I_L	Input or output leakage current per pin (sample-tested)	–	–	10	µA
C_{IN}(3)	Die input capacitance at the pad	–	–	8	pF
I_{RPU}	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 2.5V	20	–	80	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.8V	8	–	40	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.5V	5	–	30	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.2V	1	–	20	µA
I_{RPD}	Pad pull-down (when selected) @ V_{IN} = 2.5V	3	–	80	µA
I_{BATT}	Battery supply current	–	–	150	nA
n	Temperature diode ideality factor	–	1.0002	–	n
r	Series resistance	–	5	–	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. Maximum value specified for worst case process at 25°C.
3. This measurement represents the die capacitance at the pad, not including the package.

Table 4: **Typical Quiescent Supply Current *(Cont'd)***

Symbol	Description	Device	Speed and Temperature Grade						Units
			-3 (C)	-2 (C, E, & I)	-1 (C & I)	-1 (I & M)(2)	-1L (C)	-1L (I)(1)	
I_{CCOQ}	Quiescent V_{CCO} supply current	XC6VLX75T	1	1	1	N/A	1	1	mA
		XC6VLX130T	1	1	1	N/A	1	1	mA
		XC6VLX195T	1	1	1	N/A	1	1	mA
		XC6VLX240T	2	2	2	N/A	2	2	mA
		XC6VLX365T	2	2	2	N/A	2	2	mA
		XC6VLX550T(3)	N/A	3	3	N/A	3	3	mA
		XC6VLX760(3)	N/A	3	3	N/A	3	3	mA
		XC6VSX315T	2	2	2	N/A	2	2	mA
		XC6VSX475T(3)	N/A	2	2	N/A	2	2	mA
		XC6VHX250T	1	1	1	N/A	N/A	N/A	mA
		XC6VHX255T	1	1	1	N/A	N/A	N/A	mA
		XC6VHX380T(4)	2	2	2	N/A	N/A	N/A	mA
		XC6VHX565T(5)	N/A	2	2	N/A	N/A	N/A	mA
		XQ6VLX130T	N/A	1	N/A	1	N/A	1	mA
		XQ6VLX240T	N/A	2	N/A	2	N/A	2	mA
		XQ6VLX550T(7)	N/A	N/A	N/A	3	N/A	3	mA
		XQ6VSX315T	N/A	2	N/A	2	N/A	2	mA
		XQ6VSX475T(7)	N/A	N/A	N/A	2	N/A	2	mA

HT DC Specifications (HT_25)

Table 8: **HT DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply Voltage		2.38	2.5	2.63	V
V_{OD}	Differential Output Voltage for XC devices	R_T = 100 Ω across Q and $\overline{Q}$ signals	480	600	885	mV
	Differential Output Voltage for XQ devices		480	600	930	mV
ΔV_{OD}	Change in V_{OD} Magnitude		–15	–	15	mV
V_{OCM}	Output Common Mode Voltage	R_T = 100 Ω across Q and $\overline{Q}$ signals	440	600	760	mV
ΔV_{OCM}	Change in V_{OCM} Magnitude		–15	–	15	mV
V_{ID}	Input Differential Voltage		200	600	1000	mV
ΔV_{ID}	Change in V_{ID} Magnitude		–15	–	15	mV
V_{ICM}	Input Common Mode Voltage		440	600	780	mV
ΔV_{ICM}	Change in V_{ICM} Magnitude		–15	–	15	mV

LVDS DC Specifications (LVDS_25)

Table 9: **LVDS DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply Voltage		2.38	2.5	2.63	V
V_{OH}	Output High Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	–	–	1.675	V
V_{OL}	Output Low Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	0.825	–	–	V
V_{ODIFF}	Differential Output Voltage (Q – $\overline{Q}$), Q = High (Q – $\overline{Q}$), $\overline{Q}$ = High	R_T = 100 Ω across Q and $\overline{Q}$ signals	247	350	600	mV
V_{OCM}	Output Common-Mode Voltage for XC devices	R_T = 100 Ω across Q and $\overline{Q}$ signals	1.075	1.250	1.425	V
	Output Common-Mode Voltage for XQ devices		1.000	1.250	1.425	V
V_{IDIFF}	Differential Input Voltage (Q – $\overline{Q}$), Q = High (Q – $\overline{Q}$), $\overline{Q}$ = High		100	350	600	mV
V_{ICM}	Input Common-Mode Voltage		0.3	1.2	2.2	V

Extended LVDS DC Specifications (LVDSEXT_25)

Table 10: **Extended LVDS DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply Voltage		2.38	2.5	2.63	V
V_{OH}	Output High Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	–	–	1.785	V
V_{OL}	Output Low Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	0.715	–	–	V
V_{ODIFF}	Differential Output Voltage (Q – $\overline{Q}$), Q = High (Q – $\overline{Q}$), $\overline{Q}$ = High for XC devices	R_T = 100 Ω across Q and $\overline{Q}$ signals	350	–	840	mV
	Differential Output Voltage (Q – $\overline{Q}$), Q = High (Q – $\overline{Q}$), $\overline{Q}$ = High for XQ devices		350	–	850	mV
V_{OCM}	Output Common-Mode Voltage for XC devices	R_T = 100 Ω across Q and $\overline{Q}$ signals	1.075	1.250	1.425	V
	Output Common-Mode Voltage for XQ devices		1.000	1.250	1.425	V
V_{IDIFF}	Differential Input Voltage (Q – $\overline{Q}$), Q = High (Q – $\overline{Q}$), $\overline{Q}$ = High	Common-mode input voltage = 1.25V	100	–	1000	mV
V_{ICM}	Input Common-Mode Voltage	Differential input voltage = ±350 mV	0.3	1.2	2.2	V

LVPECL DC Specifications (LVPECL_25)

These values are valid when driving a 100Ω differential load only, i.e., a 100Ω resistor between the two receiver pins. The V_{OH} levels are 200 mV below standard LVPECL levels and are compatible with devices tolerant of lower common-mode ranges. Table 11 summarizes the DC output specifications of LVPECL. For more information on using LVPECL, see UG361: *Virtex-6 FPGA SelectIO Resources User Guide*.

Table 11: **LVPECL DC Specifications**

Symbol	DC Parameter	Min	Typ	Max	Units
V_{OH}	Output High Voltage	V_{CC} – 1.025	1.545	V_{CC} – 0.88	V
V_{OL}	Output Low Voltage	V_{CC} – 1.81	0.795	V_{CC} – 1.62	V
V_{ICM}	Input Common-Mode Voltage	0.6	–	2.2	V
V_{IDIFF}	Differential Input Voltage(1)(2)	0.100	–	1.5	V

Notes:

1. Recommended input maximum voltage not to exceed V_{CCAUX} + 0.2V.
2. Recommended input minimum voltage not to go below –0.5V.

eFUSE Read Endurance

Table 12 lists the maximum number of read cycle operations expected. For more information, see UG360: *Virtex-6 FPGA Configuration User Guide*.

Table 12: **eFUSE Read Endurance**

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
DNA_CYCLES	Number of DNA_PORT READ operations or JTAG ISC_DNA read command operations. Unaffected by SHIFT operations.	30,000,000				Read Cycles
AES_CYCLES	Number of JTAG FUSE_KEY or FUSE_CNTL read command operations. Unaffected by SHIFT operations.	30,000,000				Read Cycles

GTX Transceiver Specifications

GTX Transceiver DC Characteristics

Table 13: **Absolute Maximum Ratings for GTX Transceivers(1)**

Symbol	Description	Min	Max	Units
MGTAVCC	Analog supply voltage for the GTX transmitter and receiver circuits relative to GND	–0.5	1.1	V
MGTAVTT	Analog supply voltage for the GTX transmitter and receiver termination circuits relative to GND	–0.5	1.32	V
MGTAVTTRCAL	Analog supply voltage for the resistor calibration circuit of the GTX transceiver column	–0.5	1.32	V
V_{IN}	Receiver (RXP/RXN) and Transmitter (TXP/TXN) absolute input voltage	–0.5	1.32	V
$V_{MGTREFCLK}$	Reference clock absolute input voltage	–0.5	1.32	V

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.

Table 14: **Recommended Operating Conditions for GTX Transceivers(1)(2)**

Symbol	Description	Speed Grade	PLL Frequency	Min	Typ	Max	Units
MGTAVCC	Analog supply voltage for the GTX transmitter and receiver circuits relative to GND	-3, -2(3)	> 2.7 GHz	1.0	1.03	1.06	V
		-3, -2(3)	≤ 2.7 GHz	0.95	1.0	1.06	V
		-1	≤ 2.7 GHz	0.95	1.0	1.06	V
		-1L	≤ 2.7 GHz	0.95	1.0	1.05	V
MGTAVTT	Analog supply voltage for the GTX transmitter and receiver termination circuits relative to GND	All	–	1.14	1.2	1.26	V
MGTAVTTRCAL	Analog supply voltage for the resistor calibration circuit of the GTX transceiver column	All	–	1.14	1.2	1.26	V

Notes:

1. Each voltage listed requires the filter circuit described in UG366: *Virtex-6 FPGA GTX Transceivers User Guide*.
2. Voltages are specified for the temperature range of T_j = –40°C to +100°C for all XC devices and T_j = –55°C to +125°C for the XQ devices
3. If a GTX Quad contains transceivers operating with a mixture of PLL frequencies above and below 2.7 GHz, the MGTAVCC voltage supply must be in the range of 1.0V to 1.06V.

Table 15: **GTX Transceiver Supply Current (per Lane) (1)(2)**

Symbol	Description	Typ	Max	Units
$I_{MGTAVTT}$	MGTAVTT supply current for one GTX transceiver	55.9	Note 2	mA
$I_{MGTAVCC}$	MGTAVCC supply current for one GTX transceiver	56.1		mA
$MGTR_{REF}$	Precision reference resistor for internal calibration termination	100.0 ± 1% tolerance		Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C, with a 3.125 Gb/s line rate.
2. Values for currents of other transceiver configurations and conditions can be obtained by using the XPower Estimator (XPE) or XPower Analyzer (XPA) tools.

Table 21: **GTX Transceiver Reference Clock Switching Characteristics**

Symbol	Description	Conditions	All Speed Grades			Units
			Min	Typ	Max	
F_{GCLK}	Reference clock frequency range		62.5	–	650	MHz
T_{RCLK}	Reference clock rise time	20% – 80%	–	200	–	ps
T_{FCLK}	Reference clock fall time	80% – 20%	–	200	–	ps
T_{DCREF}	Reference clock duty cycle	Transceiver PLL only	45	50	55	%
T_{LOCK}	Clock recovery frequency acquisition time	Initial PLL lock	–	–	1	ms
T_{PHASE}	Clock recovery phase acquisition time	Lock to data after PLL has locked to the reference clock	–	–	200	µs

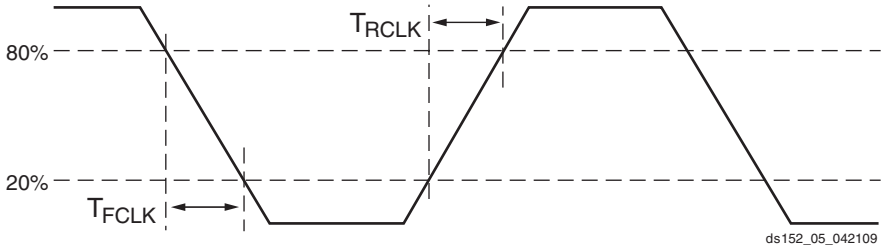

Figure 3: **Reference Clock Timing Parameters**

Table 22: **GTX Transceiver User Clock Switching Characteristics(1)**

Symbol	Description	Conditions	Speed Grade				Units
			-3	-2	-1	-1L	
F_{TXOUT}	TXOUTCLK maximum frequency	Internal 20-bit data path	330	330	250	250	MHz
		Internal 16-bit data path	412.5	412.5	312.5	250	MHz
F_{RXREC}	RXRECCLK maximum frequency	Internal 20-bit data path	330	330	250	250	MHz
		Internal 16-bit data path	412.5	412.5	312.5	250	MHz
T_{RX}	RXUSRCLK maximum frequency		412.5(2)	412.5(2)	312.5	250	MHz
T_{RX2}	RXUSRCLK2 maximum frequency	1 byte interface	376	376	312.5	250	MHz
		2 byte interface	406.25	406.25	312.5	250	MHz
		4 byte interface	206.25	206.25	156.25	125	MHz
T_{TX}	TXUSRCLK maximum frequency		412.5(3)	412.5(3)	312.5	250	MHz
T_{TX2}	TXUSRCLK2 maximum frequency	1 byte interface	376	376	312.5	250	MHz
		2 byte interface	406.25	406.25	312.5	250	MHz
		4 byte interface	206.25	206.25	156.25	125	MHz

Notes:

1. Clocking must be implemented as described in UG366: *Virtex-6 FPGA GTX Transceivers User Guide*.
2. 406.25 MHz when the RX elastic buffer is bypassed.
3. 406.25 MHz when the TX buffer is bypassed.

Table 23: **GTX Transceiver Transmitter Switching Characteristics**

Symbol	Description	Condition	Min	Typ	Max	Units
F_{GTXTX}	Serial data rate range		0.480	–	F_{GTXMAX}	Gb/s
T_{RTX}	TX Rise time	20%–80%	–	120	–	ps
T_{FTX}	TX Fall time	80%–20%	–	120	–	ps
T_{LLSKEW}	TX lane-to-lane skew(1)		–	–	350	ps
$V_{TXOOBVDPP}$	Electrical idle amplitude		–	–	15	mV
$T_{TXOOBTRANSITION}$	Electrical idle transition time		–	–	75	ns
$TJ_{6.5}$	Total Jitter(2)(3)	6.5 Gb/s	–	–	0.33	UI
$DJ_{6.5}$	Deterministic Jitter(2)(3)		–	–	0.17	UI
$TJ_{5.0}$	Total Jitter(2)(3)	5.0 Gb/s	–	–	0.33	UI
$DJ_{5.0}$	Deterministic Jitter(2)(3)		–	–	0.15	UI
$TJ_{4.25}$	Total Jitter(2)(3)	4.25 Gb/s	–	–	0.33	UI
$DJ_{4.25}$	Deterministic Jitter(2)(3)		–	–	0.14	UI
$TJ_{3.75}$	Total Jitter(2)(3)	3.75 Gb/s	–	–	0.34	UI
$DJ_{3.75}$	Deterministic Jitter(2)(3)		–	–	0.16	UI
$TJ_{3.125}$	Total Jitter(2)(3)	3.125 Gb/s	–	–	0.2	UI
$DJ_{3.125}$	Deterministic Jitter(2)(3)		–	–	0.1	UI
$TJ_{3.125L}$	Total Jitter(2)(3)	3.125 Gb/s(4)	–	–	0.35	UI
$DJ_{3.125L}$	Deterministic Jitter(2)(3)		–	–	0.16	UI
$TJ_{2.5}$	Total Jitter(2)(3)	2.5 Gb/s(5)	–	–	0.20	UI
$DJ_{2.5}$	Deterministic Jitter(2)(3)		–	–	0.08	UI
$TJ_{1.25}$	Total Jitter(2)(3)	1.25 Gb/s(6)	–	–	0.15	UI
$DJ_{1.25}$	Deterministic Jitter(2)(3)		–	–	0.06	UI
TJ_{600}	Total Jitter(2)(3)	600 Mb/s	–	–	0.1	UI
DJ_{600}	Deterministic Jitter(2)(3)		–	–	0.03	UI
TJ_{480}	Total Jitter(2)(3)	480 Mb/s	–	–	0.1	UI
DJ_{480}	Deterministic Jitter(2)(3)		–	–	0.03	UI

Notes:

1. Using same REFCLK input with TXENPMAPHASEALIGN enabled for up to 12 consecutive transmitters (three fully populated GTX Quads).
2. Using PLL_DIVSEL_FB = 2, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
3. All jitter values are based on a bit-error ratio of $1e^{-12}$.
4. PLL frequency at 1.5625 GHz and OUTDIV = 1.
5. PLL frequency at 2.5 GHz and OUTDIV = 2.
6. PLL frequency at 2.5 GHz and OUTDIV = 4.

Figure 4 shows the timing parameters in Table 27.

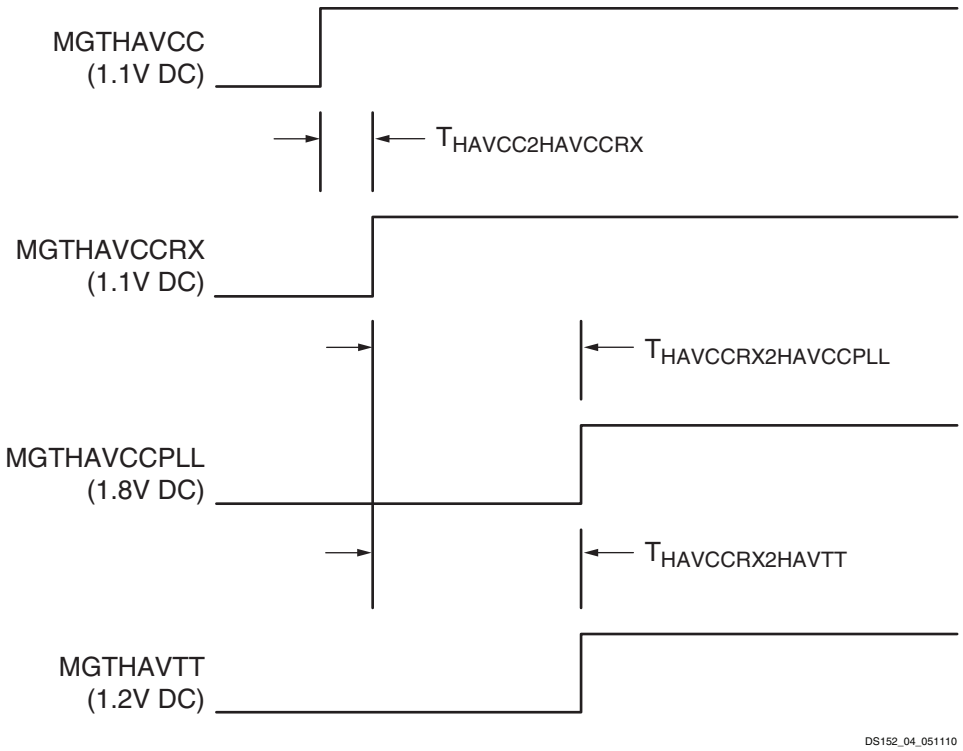

Figure 4: **GTH Transceiver Power Supply Power-On Sequencing**

Table 28: **GTH Transceiver Supply Current**

Symbol	Description	Typ(1)	Max	Units
$I_{MGTHAVCC}$	MGTHAVCC supply current for one GTH Quad (4 lanes)	571	Note 2	mA
$I_{MGTHAVCCRX}$	MGTHAVCCRX supply current for a GTH Quad (4 lanes)	254	Note 2	mA
$I_{MGTHAVTT}$	MGTHAVTT supply current for one GTH Quad (4 lanes)	93	Note 2	mA
$I_{MGTHAVCCPLL}$	MGTHAVCCPLL supply current for one GTH Quad (4 lanes)	219	Note 2	mA
$MGTR_{REF}$	Precision reference resistor for internal calibration termination	1000.0 ± 1% tolerance		Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C, with a 10.3125 Gb/s line rate.
2. Values for currents other than the values specified in this table can be obtained by using the XPower Estimator (XPE) or XPower Analyzer (XPA) tools.

Table 29: **GTH Transceiver Quiescent Supply Current(1)(2)**

Symbol	Description	Typ(3)	Max	Units
$I_{MGTHAVCCQ}$	Quiescent MGTHAVCC Supply Current for one GTH Quad (4 lanes)	65	Note 4	mA
$I_{MGTHAVCCRXQ}$	Quiescent MGTHAVCCRX Supply Current for one GTH Quad (4 lanes)	17	Note 4	mA
$I_{MGTHAVTTQ}$	Quiescent MGTHAVTT Supply Current for one GTH Quad (4 lanes)	1	Note 4	mA
$I_{MGTHAVCCPLLQ}$	Quiescent MGTHAVCCPLL Supply Current for one GTH Quad (4 lanes)	1	Note 4	mA

Notes:

1. Device powered and unconfigured.
2. GTH transceiver quiescent supply current for an entire device can be calculated by multiplying the values in this table by the number of available GTH transceivers.
3. Typical values are specified at nominal voltage, 25°C.
4. Currents for conditions other than values specified in this table can be obtained by using the XPE or XPA tools.

Table 35: **GTH Transceiver User Clock Switching Characteristics (1)**

Symbol	Description	Conditions	Speed Grade			Units
			-3	-2	-1	
F_{TXOUT}	TXUSERCLKOUT maximum frequency		350	350	323	MHz
F_{RXOUT}	RXUSERCLKOUT maximum frequency		350	350	323	MHz
F_{TXIN}	TXUSERCLKIN maximum frequency	16-bit data path	350	350	323	MHz
		20-bit data path	280	280	258	MHz
		32-bit data path	350	350	323	MHz
		40-bit data path	280	280	258	MHz
		64-bit data path	175	175	162	MHz
		80-bit data path	140	140	129	MHz
		64B/66B-bit data path	170	170	157	MHz
F_{RXIN}	RXUSERCLKIN maximum frequency	16-bit data path	350	350	323	MHz
		20-bit data path	280	280	258	MHz
		32-bit data path	350	350	323	MHz
		40-bit data path	280	280	258	MHz
		64-bit data path	175	175	162	MHz
		80-bit data path	140	140	129	MHz
		64B/66B-bit data path	170	170	157	MHz

Notes:

1. Clocking must be implemented as described in UG371:*Virtex-6 FPGA GTH Transceivers User Guide*.

Table 36: **GTH Transceiver Transmitter Switching Characteristics**

Symbol	Description	Condition	Min	Typ	Max	Units
T_{RTX}	TX Rise time	20%–80%	–	50(3)	–	ps
T_{FTX}	TX Fall time	80%–20%	–	50(3)	–	ps
T_{LLSKEW}	TX lane-to-lane skew	within one GTH Quad	–	–	300	ps
Transmitter Output Jitter(1)(2)						
$TJ_{11.18}$	Total Jitter	11.181 Gb/s	–	–	0.280	UI
$DJ_{11.18}$	Deterministic Jitter		–	–	0.170	UI
$TJ_{10.3125}$	Total Jitter	10.3125 Gb/s	–	–	0.280	UI
$DJ_{10.3125}$	Deterministic Jitter		–	–	0.170	UI
$TJ_{9.953}$	Total Jitter	9.953 Gb/s	–	–	0.280	UI
$DJ_{9.953}$	Deterministic Jitter		–	–	0.170	UI
$TJ_{2.667}$	Total Jitter	2.667 Gb/s	–	–	0.110	UI
$DJ_{2.667}$	Deterministic Jitter		–	–	0.060	UI
$TJ_{2.488}$	Total Jitter	2.488 Gb/s	–	–	0.110	UI
$DJ_{2.488}$	Deterministic Jitter		–	–	0.060	UI

Notes:

1. These values are NOT intended for protocol specific compliance determinations.
2. All jitter values are based on a bit-error ratio of $1e^{-12}$.
3. Rise and fall times are specified at the transmitter package balls.

Table 44: **IOB Switching Characteristics for the Commercial (XC) Virtex-6 Devices *(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	-3	-2	-1	-1L	-3	-2	-1	-1L	-3	-2	-1	-1L	
LVCMOS25, Fast, 24 mA	0.51	0.57	0.66	0.70	1.66	1.79	1.99	1.96	1.66	1.79	1.99	1.96	ns
LVCMOS18, Slow, 2 mA	0.55	0.61	0.71	0.73	4.21	4.47	4.87	4.30	4.21	4.47	4.87	4.30	ns
LVCMOS18, Slow, 4 mA	0.55	0.61	0.71	0.73	2.79	2.96	3.21	2.94	2.79	2.96	3.21	2.94	ns
LVCMOS18, Slow, 6 mA	0.55	0.61	0.71	0.73	2.30	2.43	2.64	2.47	2.30	2.43	2.64	2.47	ns
LVCMOS18, Slow, 8 mA	0.55	0.61	0.71	0.73	2.01	2.11	2.27	2.24	2.01	2.11	2.27	2.24	ns
LVCMOS18, Slow, 12 mA	0.55	0.61	0.71	0.73	1.88	1.99	2.15	2.10	1.88	1.99	2.15	2.10	ns
LVCMOS18, Slow, 16 mA	0.55	0.61	0.71	0.73	1.84	1.95	2.11	2.04	1.84	1.95	2.11	2.04	ns
LVCMOS18, Fast, 2 mA	0.55	0.61	0.71	0.73	4.00	4.23	4.57	4.08	4.00	4.23	4.57	4.08	ns
LVCMOS18, Fast, 4 mA	0.55	0.61	0.71	0.73	2.62	2.76	2.97	2.74	2.62	2.76	2.97	2.74	ns
LVCMOS18, Fast, 6 mA	0.55	0.61	0.71	0.73	2.15	2.28	2.46	2.32	2.15	2.28	2.46	2.32	ns
LVCMOS18, Fast, 8 mA	0.55	0.61	0.71	0.73	1.90	1.99	2.13	2.14	1.90	1.99	2.13	2.14	ns
LVCMOS18, Fast, 12 mA	0.55	0.61	0.71	0.73	1.69	1.80	1.97	1.88	1.69	1.80	1.97	1.88	ns
LVCMOS18, Fast, 16 mA	0.55	0.61	0.71	0.73	1.63	1.74	1.91	1.88	1.63	1.74	1.91	1.88	ns
LVCMOS15, Slow, 2 mA	0.64	0.73	0.85	0.85	3.43	3.77	4.29	3.91	3.43	3.77	4.29	3.91	ns
LVCMOS15, Slow, 4 mA	0.64	0.73	0.85	0.85	2.58	2.79	3.10	2.93	2.58	2.79	3.10	2.93	ns
LVCMOS15, Slow, 6 mA	0.64	0.73	0.85	0.85	2.08	2.32	2.68	2.50	2.08	2.32	2.68	2.50	ns
LVCMOS15, Slow, 8 mA	0.64	0.73	0.85	0.85	1.81	1.98	2.23	2.24	1.81	1.98	2.23	2.24	ns
LVCMOS15, Slow, 12 mA	0.64	0.73	0.85	0.85	1.76	1.91	2.13	2.07	1.76	1.91	2.13	2.07	ns
LVCMOS15, Slow, 16 mA	0.64	0.73	0.85	0.85	1.69	1.83	2.04	1.98	1.69	1.83	2.04	1.98	ns
LVCMOS15, Fast, 2 mA	0.64	0.73	0.85	0.85	3.44	3.77	4.28	3.91	3.44	3.77	4.28	3.91	ns
LVCMOS15, Fast, 4 mA	0.64	0.73	0.85	0.85	2.37	2.53	2.78	2.66	2.37	2.53	2.78	2.66	ns
LVCMOS15, Fast, 6 mA	0.64	0.73	0.85	0.85	1.80	2.05	2.42	2.16	1.80	2.05	2.42	2.16	ns
LVCMOS15, Fast, 8 mA	0.64	0.73	0.85	0.85	1.76	1.90	2.11	2.04	1.76	1.90	2.11	2.04	ns
LVCMOS15, Fast, 12 mA	0.64	0.73	0.85	0.85	1.64	1.77	1.97	1.90	1.64	1.77	1.97	1.90	ns
LVCMOS15, Fast, 16 mA	0.64	0.73	0.85	0.85	1.62	1.76	1.96	1.92	1.62	1.76	1.96	1.92	ns
LVCMOS12, Slow, 2 mA	0.72	0.81	0.93	0.95	3.14	3.39	3.75	3.54	3.14	3.39	3.75	3.54	ns
LVCMOS12, Slow, 4 mA	0.72	0.81	0.93	0.95	2.43	2.63	2.93	2.79	2.43	2.63	2.93	2.79	ns
LVCMOS12, Slow, 6 mA	0.72	0.81	0.93	0.95	1.92	2.11	2.41	2.26	1.92	2.11	2.41	2.26	ns
LVCMOS12, Slow, 8 mA	0.72	0.81	0.93	0.95	1.87	2.02	2.25	2.17	1.87	2.02	2.25	2.17	ns
LVCMOS12, Fast, 2 mA	0.72	0.81	0.93	0.95	2.71	2.98	3.39	3.11	2.71	2.98	3.39	3.11	ns
LVCMOS12, Fast, 4 mA	0.72	0.81	0.93	0.95	1.93	2.16	2.51	2.31	1.93	2.16	2.51	2.31	ns
LVCMOS12, Fast, 6 mA	0.72	0.81	0.93	0.95	1.75	1.89	2.11	2.05	1.75	1.89	2.11	2.05	ns
LVCMOS12, Fast, 8 mA	0.72	0.81	0.93	0.95	1.69	1.82	2.02	1.98	1.69	1.82	2.02	1.98	ns
LVDCI_25	0.51	0.57	0.66	0.70	2.05	2.14	2.26	2.26	2.05	2.14	2.26	2.26	ns
LVDCI_18	0.55	0.61	0.71	0.73	2.07	2.23	2.47	2.38	2.07	2.23	2.47	2.38	ns
LVDCI_15	0.64	0.73	0.85	0.85	1.85	2.01	2.24	2.18	1.85	2.01	2.24	2.18	ns

Table 44: **IOB Switching Characteristics for the Commercial (XC) Virtex-6 Devices *(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	-3	-2	-1	-1L	-3	-2	-1	-1L	-3	-2	-1	-1L	
DIFF_SSTL18_I	0.85	0.94	1.09	1.08	1.47	1.58	1.75	1.73	1.47	1.58	1.75	1.73	ns
DIFF_SSTL18_I_DCI	0.85	0.94	1.09	1.08	1.40	1.51	1.67	1.65	1.40	1.51	1.67	1.65	ns
DIFF_SSTL18_II	0.85	0.94	1.09	1.08	1.39	1.50	1.67	1.66	1.39	1.50	1.67	1.66	ns
DIFF_SSTL18_II_DCI	0.85	0.94	1.09	1.08	1.36	1.47	1.63	1.62	1.36	1.47	1.63	1.62	ns
DIFF_SSTL18_II_T_DCI	0.85	0.94	1.09	1.08	1.40	1.51	1.67	1.65	1.40	1.51	1.67	1.65	ns
DIFF_SSTL15	0.81	0.91	1.06	1.06	1.42	1.54	1.71	1.69	1.42	1.54	1.71	1.69	ns
DIFF_SSTL15_DCI	0.81	0.91	1.06	1.06	1.41	1.52	1.68	1.66	1.41	1.52	1.68	1.66	ns
DIFF_SSTL15_T_DCI	0.81	0.91	1.06	1.06	1.41	1.52	1.68	1.66	1.41	1.52	1.68	1.66	ns

Table 45: **IOB Switching Characteristics for the Defense-grade (XQ) Virtex-6 Devices**

I/O Standard	T_{IOPI}			T_{IOOP}			T_{IOTP}			Units
	Speed Grade			Speed Grade			Speed Grade			
	-2	-1	-1L	-2	-1	-1L	-2	-1	-1L	
LVDS_25	0.94	1.09	1.08	1.54	2.16	1.62	1.54	2.16	1.62	ns
LVDSEXT_25	0.94	1.09	1.08	1.65	2.20	1.73	1.65	2.20	1.73	ns
HT_25	0.94	1.09	1.08	1.62	2.20	1.69	1.62	2.20	1.69	ns
BLVDS_25	0.94	1.09	1.08	1.50	3.18	1.65	1.50	3.18	1.65	ns
RSDS_25 (point to point)	0.94	1.09	1.08	1.54	2.22	1.62	1.54	2.22	1.62	ns
HSTL_I	0.91	1.06	1.06	1.56	2.44	1.71	1.56	2.44	1.71	ns
HSTL_II	0.91	1.06	1.06	1.56	2.21	1.72	1.56	2.21	1.72	ns
HSTL_III	0.91	1.06	1.06	1.54	2.50	1.69	1.54	2.50	1.69	ns
HSTL_I_18	0.91	1.06	1.06	1.58	2.43	1.72	1.58	2.43	1.72	ns
HSTL_II_18	0.91	1.06	1.06	1.62	2.30	1.78	1.62	2.30	1.78	ns
HSTL_III_18	0.91	1.06	1.06	1.54	2.49	1.69	1.54	2.49	1.69	ns
SSTL2_I	0.91	1.06	1.06	1.60	2.50	1.74	1.60	2.50	1.74	ns
SSTL2_II	0.91	1.06	1.06	1.54	2.49	1.71	1.54	2.49	1.71	ns
SSTL15	0.91	1.06	1.06	1.54	2.07	1.69	1.54	2.07	1.69	ns
LVCMOS25, Slow, 2 mA	0.57	0.66	0.70	5.46	6.01	5.63	5.46	6.01	5.63	ns
LVCMOS25, Slow, 4 mA	0.57	0.66	0.70	3.49	3.79	3.65	3.49	3.79	3.65	ns
LVCMOS25, Slow, 6 mA	0.57	0.66	0.70	2.81	3.08	2.95	2.81	3.08	2.95	ns
LVCMOS25, Slow, 8 mA	0.57	0.66	0.70	2.41	2.72	2.59	2.41	2.72	2.59	ns
LVCMOS25, Slow, 12 mA	0.57	0.66	0.70	1.95	2.23	2.10	1.95	2.23	2.10	ns
LVCMOS25, Slow, 16 mA	0.57	0.66	0.70	2.05	2.29	2.21	2.05	2.29	2.21	ns
LVCMOS25, Slow, 24 mA	0.57	0.66	0.70	1.82	2.24	1.98	1.82	2.24	1.98	ns
LVCMOS25, Fast, 2 mA	0.57	0.66	0.70	5.49	6.04	5.62	5.49	6.04	5.62	ns
LVCMOS25, Fast, 4 mA	0.57	0.66	0.70	3.50	3.82	3.65	3.50	3.82	3.65	ns
LVCMOS25, Fast, 6 mA	0.57	0.66	0.70	2.73	2.99	2.88	2.73	2.99	2.88	ns
LVCMOS25, Fast, 8 mA	0.57	0.66	0.70	2.33	2.65	2.53	2.33	2.65	2.53	ns
LVCMOS25, Fast, 12 mA	0.57	0.66	0.70	1.88	2.08	2.03	1.88	2.08	2.03	ns

Input Serializer/Deserializer Switching Characteristics

Table 51: **ISERDES Switching Characteristics**

Symbol	Description	Speed Grade					Units
		-3	-2	-1 (XC)	-1 (XQ)	-1L	
Setup/Hold for Control Lines							
$T_{ISCCK\_BITSLIP}$/ $T_{ISCKC\_BITSLIP}$	BITSLIP pin Setup/Hold with respect to CLKDIV	0.07/ 0.15	0.08/ 0.16	0.09/ 0.17	0.09/ 0.17	0.14/ 0.17	ns
T_{ISCCK_CE} / T_{ISCKC_CE}(2)	CE pin Setup/Hold with respect to CLK (for CE1)	0.20/ 0.03	0.25/ 0.04	0.27/ 0.04	0.27/ 0.04	0.31/ 0.05	ns
T_{ISCCK_CE2} / T_{ISCKC_CE2}(2)	CE pin Setup/Hold with respect to CLKDIV (for CE2)	0.01/ 0.27	0.01 0.29	0.01/ 0.31	0.01/ 0.31	–0.05/ 0.35	ns
Setup/Hold for Data Lines							
T_{ISDCK_D} /T_{ISCKD_D}	D pin Setup/Hold with respect to CLK	0.07/ 0.08	0.08/ 0.09	0.09/ 0.11	0.09/ 0.11	0.11/ 0.19	ns
T_{ISDCK_DDLY} /T_{ISCKD_DDLY}	DDLY pin Setup/Hold with respect to CLK (using IODELAY)(1)	0.10/ 0.05	0.12/ 0.06	0.14/ 0.07	0.14/ 0.07	0.16/ 0.15	ns
$T_{ISDCK\_D\_DDR}$ /$T_{ISCKD\_D\_DDR}$	D pin Setup/Hold with respect to CLK at DDR mode	0.07/ 0.08	0.08/ 0.09	0.09/ 0.11	0.09/ 0.11	0.11/ 0.19	ns
$T_{ISDCK\_DDLY\_DDR}$ $T_{ISCKD\_DDLY\_DDR}$	D pin Setup/Hold with respect to CLK at DDR mode (using IODELAY)(1)	0.10/ 0.05	0.12/ 0.06	0.14/ 0.07	0.14/ 0.07	0.16/ 0.15	ns
Sequential Delays							
T_{ISCKO_Q}	CLKDIV to out at Q pin	0.57	0.66	0.75	0.80	0.88	ns
Propagation Delays							
T_{ISDO_DO}	D input to DO output pin	0.19	0.22	0.25	0.25	0.28	ns

Notes:

1. Recorded at 0 tap value.
2. T_{ISCCK_CE2} and T_{ISCKC_CE2} are reported as T_{ISCCK_CE}/T_{ISCKC_CE} in TRACE report.

Table 57: **Block RAM and FIFO Switching Characteristics *(Cont'd)***

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
T_{RCCK_WE}/T_{RCKC_WE}	Write Enable (WE) input (Block RAM only)	0.44/ 0.19	0.47/ 0.25	0.52/ 0.35	0.67/ 0.24	ns, Min
$T_{RCCK\_WREN}/T_{RCKC\_WREN}$	WREN FIFO inputs	0.47/ 0.26	0.50/ 0.27	0.55/ 0.30	0.68/ 0.31	ns, Min
$T_{RCCK\_RDEN}/T_{RCKC\_RDEN}$	RDEN FIFO inputs	0.46/ 0.26	0.50/ 0.27	0.55/ 0.30	0.67/ 0.31	ns, Min
Reset Delays						
T_{RCO_FLAGS}	Reset RST to FIFO Flags/Pointers(10)	0.90	0.98	1.10	1.23	ns, Max
$T_{RCCK\_RSTREG}/T_{RCKC\_RSTREG}$	FIFO reset timing(11)	0.22/ 0.23	0.24/ 0.24	0.28/ 0.26	0.31/ 0.27	ns, Min
Maximum Frequency						
F_{MAX}	Block RAM in TDP and SDP modes (Write First and No Change modes)	600	540	450	340	MHz
	Block RAM (Read First mode)	525	475	400	275	MHz
	Block RAM (SDP mode)(12)	525	475	400	275	MHz
$F_{MAX\_CASCADE}$	Block RAM Cascade (Write First and No Change modes)	550	490	400	300	MHz
	Block RAM Cascade (Read First mode)	475	425	350	235	MHz
F_{MAX_FIFO}	FIFO in all modes	600	540	450	340	MHz
F_{MAX_ECC}	Block RAM and FIFO in ECC configuration	450	400	325	250	MHz

Notes:

1. TRACE will report all of these parameters as T_{RCKO_DO}.
2. T_{RCKO_DOR} includes T_{RCKO_DOW}, T_{RCKO_DOPR}, and T_{RCKO_DOPW} as well as the B port equivalent timing parameters.
3. These parameters also apply to synchronous FIFO with DO_REG = 0.
4. T_{RCKO_DO} includes T_{RCKO_DOP} as well as the B port equivalent timing parameters.
5. These parameters also apply to multirate (asynchronous) and synchronous FIFO with DO_REG = 1.
6. T_{RCKO_FLAGS} includes the following parameters: T_{RCKO_AEMPTY}, T_{RCKO_AFULL}, T_{RCKO_EMPTY}, T_{RCKO_FULL}, T_{RCKO_RDERR}, T_{RCKO_WRERR}.
7. $T_{RCKO\_POINTERS}$ includes both $T_{RCKO\_RDCOUNT}$ and $T_{RCKO\_WRCOUNT}$.
8. The ADDR setup and hold must be met when EN is asserted (even when WE is deasserted). Otherwise, block RAM data corruption is possible.
9. T_{RCKO_DI} includes both A and B inputs as well as the parity inputs of A and B.
10. T_{RCO_FLAGS} includes the following flags: AEMPTY, AFULL, EMPTY, FULL, RDERR, WRERR, RDCOUNT, and WRCOUNT.
11. The FIFO reset must be asserted for at least three positive clock edges.
12. When using ISE software v12.4 or later, if the RDADDR_COLLISION_HWCONFIG attribute is set to PERFORMANCE or the block RAM is in single-port operation, then the faster F_{MAX} for WRITE_FIRST/NO_CHANGE modes apply.

Table 58: **DSP48E1 Switching Characteristics *(Cont'd)***

Symbol	Description	Speed Grade					Units
		-3	-2	-1 (XC)	-1 (XQ)	-1L	
Maximum Frequency							
F_{MAX}	With all registers used	600	540	450	450	410	MHz
F_{MAX_PATDET}	With pattern detector	551	483	408	408	356	MHz
$F_{MAX\_MULT\_NOMREG}$	Two register multiply without MREG	356	311	262	262	224	MHz
$F_{MAX\_MULT\_NOMREG\_PATDET}$	Two register multiply without MREG with pattern detect	327	286	241	241	211	MHz
$F_{MAX\_PREADD\_MULT\_NOADREG}$	Without ADREG	398	347	292	292	254	MHz
$F_{MAX\_PREADD\_MULT\_NOADREG\_PATDET}$	Without ADREG with pattern detect	398	347	292	292	254	MHz
$F_{MAX\_NOPIPELINEREG}$	Without pipeline registers (MREG, ADREG)	266	233	196	196	171	MHz
$F_{MAX\_NOPIPELINEREG\_PATDET}$	Without pipeline registers (MREG, ADREG) with pattern detect	250	219	184	184	160	MHz

Configuration Switching Characteristics

Table 59: **Configuration Switching Characteristics**

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
Power-up Timing Characteristics						
T_{PL}(1)	Program Latency	5	5	5	5	ms, Max
T_{POR}(1)	Power-on-Reset	15/55	15/55	15/55	15/60	ms, Min/Max
T_{ICCK}	CCLK (output) delay	400	400	400	400	ns, Min
$T_{PROGRAM}$	Program Pulse Width	250	250	250	250	ns, Min
Master/Slave Serial Mode Programming Switching						
T_{DCCK}/T_{CCKD}	DIN Setup/Hold, slave mode	4.0/0.0	4.0/0.0	4.0/0.0	4.5/0.0	ns, Min
T_{DSCCK}/T_{SCCKD}	DIN Setup/Hold, master mode	4.0/0.0	4.0/0.0	4.0/0.0	5.0/0.0	ns, Min
T_{CCO}	DOUT at 2.5V	6	6	6	7	ns, Max
	DOUT at 1.8V	6	6	6	7	ns, Max
F_{MCCK}	Maximum CCLK frequency, serial modes	105	105	105	70	MHz, Max
$F_{MCCKTOL}$	Frequency Tolerance, master mode with respect to nominal CCLK.	55	55	55	60	%
F_{MSCCK}	Slave mode external CCLK	100	100	100	100	MHz
SelectMAP Mode Programming Switching						
T_{SMDCCK}/T_{SMCCKD}	SelectMAP Data Setup/Hold	4.0/0.0	4.0/0.0	4.0/0.0	5.5/0.0	ns, Min
$T_{SMCSCCK}/T_{SMCCKCS}$	CSI_B Setup/Hold	4.0/0.0	4.0/0.0	4.0/0.0	5.5/0.0	ns, Min
T_{SMCCKW}/T_{SMWCCK}	RDWR_B Setup/Hold	10.0/0.0	10.0/0.0	10.0/0.0	16.0/0.0	ns, Min
$T_{SMCKCSO}$	CSO_B clock to out (330 Ω pull-up resistor required)	6	6	6	7	ns, Max
T_{SMCO}	CCLK to DATA out in readback at 2.5V	6	6	6	7	ns, Max
	CCLK to DATA out in readback at 1.8V	6	6	6	7	ns, Max

Table 59: **Configuration Switching Characteristics *(Cont'd)***

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
$T_{MMCMDCK\_DI}$/ $T_{MMCMCKD\_DI}$	DI Setup/Hold	1.25/ 0.00	1.40/ 0.00	1.63/ 0.00	1.64/ 0.00	ns
$T_{MMCMDCK\_DEN}$/ $T_{MMCMCKD\_DEN}$	DEN Setup/Hold time	1.25/ 0.00	1.40/ 0.00	1.63/ 0.00	1.64/ 0.00	ns
$T_{MMCMDCK\_DWE}$/ $T_{MMCMCKD\_DWE}$	DWE Setup/Hold time	1.25/ 0.00	1.40/ 0.00	1.63/ 0.00	1.64/ 0.00	ns
$T_{MMCMCKO\_DO}$	CLK to out of DO(3)	2.60	3.02	3.64	3.68	ns
$T_{MMCMCKO\_DRDY}$	CLK to out of DRDY	0.32	0.34	0.38	0.38	ns

Notes:

1. To support longer delays in configuration, use the design solutions described in UG360: *Virtex-6 FPGA Configuration User Guide*.
2. Only during configuration, the last edge is determined by a weak pull-up/pull-down resistor in the I/O.
3. DO will hold until next DRP operation.

Clock Buffers and Networks

Table 60: **Global Clock Switching Characteristics (Including BUFGCTRL)**

Symbol	Description	Devices	Speed Grade				Units
			-3	-2	-1	-1L	
$T_{BCCCK\_CE}/T_{BCCKC\_CE}$(1)	CE pins Setup/Hold	All	0.11/ 0.00	0.13/ 0.00	0.16/ 0.00	0.13/ 0.00	ns
T_{BCCCK_S}/T_{BCCKC_S}(1)	S pins Setup/Hold	All	0.11/ 0.00	0.13/ 0.00	0.16/ 0.00	0.13/ 0.00	ns
T_{BCCKO_O}(2)	BUFGCTRL delay from I0/I1 to O	All	0.07	0.08	0.10	0.10	ns
Maximum Frequency							
F_{MAX}	Global clock tree (BUFG)	All except LX760	800	750	700	667	MHz
		LX760	N/A	700	700	667	MHz

Notes:

1. T_{BCCCK_CE} and T_{BCCKC_CE} must be satisfied to assure glitch-free operation of the global clock when switching between clocks. These parameters do not apply to the BUFGMUX_VIRTEX4 primitive that assures glitch-free operation. The other global clock setup and hold times are optional; only needing to be satisfied if device operation requires simulation matches on a cycle-for-cycle basis when switching between clocks.
2. T_{BGCKO_O} (BUFG delay from I0 to O) values are the same as T_{BCCKO_O} values.

Table 61: **Input/Output Clock Switching Characteristics (BUFIO)**

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
T_{BIOCKO_O}	Clock to out delay from I to O	0.14	0.16	0.18	0.21	ns
Maximum Frequency						
F_{MAX}	I/O clock tree (BUFIO)	800	800	710	710	MHz

Table 62: **Regional Clock Switching Characteristics (BUFR)**

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
T_{BRCKO_O}	Clock to out delay from I to O	0.56	0.62	0.73	0.82	ns
$T_{BRCKO\_O\_BYP}$	Clock to out delay from I to O with Divide Bypass attribute set	0.28	0.31	0.36	0.41	ns

Table 62: **Regional Clock Switching Characteristics (BUFR) *(Cont'd)***

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
T_{BRDO_O}	Propagation delay from CLR to O	0.69	0.74	0.80	1.12	ns
Maximum Frequency						
F_{MAX}[1]	Regional clock tree (BUFR)	500	420	300	300	MHz

Notes:

1. The maximum input frequency to the BUFR is the BUFIO F_{MAX} frequency.

Table 63: **Horizontal Clock Buffer Switching Characteristics (BUFH)**

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
T_{BHCKO_O}	BUFH delay from I to O	0.10	0.11	0.13	0.15	ns
$T_{BHCCK\_CE}/T_{BHCKC\_CE}$	CE pin Setup and Hold	0.04/ 0.04	0.04/ 0.04	0.05/ 0.05	0.04/ 0.04	ns
Maximum Frequency						
F_{MAX}	Horizontal clock buffer (BUFH)	800	750	700	667	MHz

MMCM Switching Characteristics

Table 64: **MMCM Specification**

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
F_{INMAX}	Maximum Input Clock Frequency[1]	800	750	700	700	MHz
F_{INMIN}	Minimum Input Clock Frequency	10	10	10	10	MHz
$F_{INJITTER}$	Maximum Input Clock Period Jitter	< 20% of clock input period or 1 ns Max				
F_{INDUTY}[2]	Allowable Input Duty Cycle: 10—49 MHz	25/75				%
	Allowable Input Duty Cycle: 50—199 MHz	30/70				%
	Allowable Input Duty Cycle: 200—399 MHz	35/65				%
	Allowable Input Duty Cycle: 400—499 MHz	40/60				%
	Allowable Input Duty Cycle: >500 MHz	45/55				%
F_{MIN_PSCLK}	Minimum Dynamic Phase Shift Clock Frequency	0.01	0.01	0.01	0.01	MHz
F_{MAX_PSCLK}	Maximum Dynamic Phase Shift Clock Frequency	550	500	450	450	MHz
F_{VCOMIN}	Minimum MMCM VCO Frequency	600	600	600	600	MHz
F_{VCOMAX}	Maximum MMCM VCO Frequency	1600	1440	1200	1200	MHz
$F_{BANDWIDTH}$	Low MMCM Bandwidth at Typical[3]	1.00	1.00	1.00	1.00	MHz
	High MMCM Bandwidth at Typical[3]	4.00	4.00	4.00	4.00	MHz
$T_{STATPHAOFFSET}$	Static Phase Offset of the MMCM Outputs[4]	0.12	0.12	0.12	0.12	ns
$T_{OUTJITTER}$	MMCM Output Jitter[5]	Note 3				
$T_{OUTDUTY}$	MMCM Output Clock Duty Cycle Precision[6]	0.15	0.20	0.20	0.20	ns
$T_{LOCKMAX}$	MMCM Maximum Lock Time	100	100	100	100	µs
F_{OUTMAX}	MMCM Maximum Output Frequency	800	750	700	700	MHz
F_{OUTMIN}	MMCM Minimum Output Frequency[7][8]	4.69	4.69	4.69	4.69	MHz
$T_{EXTFDVAR}$	External Clock Feedback Variation	< 20% of clock input period or 1 ns Max				

Virtex-6 Device Pin-to-Pin Output Parameter Guidelines

All devices are 100% functionally tested. The representative values for typical pin locations and normal clock loading are listed in Table 65. Values are expressed in nanoseconds unless otherwise noted.

Table 65: **Global Clock Input to Output Delay Without MMCM**

Symbol	Description	Device	Speed Grade				Units
			-3	-2	-1	-1L	
LVCMOS25 Global Clock Input to Output Delay using Output Flip-Flop, 12mA, Fast Slew Rate, *without* MMCM.							
T_{ICKOF}	Global Clock input and OUTFF *without* MMCM	XC6VLX75T	4.91	5.32	5.88	6.02	ns
		XC6VLX130T	4.89	5.33	6.00	6.13	ns
		XC6VLX195T	5.02	5.46	6.13	6.27	ns
		XC6VLX240T	5.02	5.46	6.13	6.27	ns
		XC6VLX365T	5.30	5.75	6.43	6.37	ns
		XC6VLX550T	N/A	6.02	6.72	6.60	ns
		XC6VLX760	N/A	6.26	6.97	6.87	ns
		XC6VSX315T	5.40	5.85	6.54	6.49	ns
		XC6VSX475T	N/A	6.01	6.71	6.61	ns
		XC6VHX250T	5.18	5.63	6.30	N/A	ns
		XC6VHX255T	5.20	5.66	6.34	N/A	ns
		XC6VHX380T	5.38	5.84	6.53	N/A	ns
		XC6VHX565T	N/A	6.03	6.71	N/A	ns
		XQ6VLX130T	N/A	5.33	6.00	6.13	ns
		XQ6VLX240T	N/A	5.46	6.13	6.27	ns
		XQ6VLX550T	N/A	N/A	6.72	6.60	ns
		XQ6VSX315T	N/A	5.85	6.54	6.49	ns
		XQ6VSX475T	N/A	N/A	6.71	6.61	ns

Notes:

1. Listed above are representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.

Virtex-6 Device Pin-to-Pin Input Parameter Guidelines

All devices are 100% functionally tested. The representative values for typical pin locations and normal clock loading are listed in Table 68. Values are expressed in nanoseconds unless otherwise noted.

Table 68: **Global Clock Input Setup and Hold Without MMCM**

Symbol	Description	Device	Speed Grade				Units
			-3	-2	-1	-1L	
Input Setup and Hold Time Relative to Global Clock Input Signal for LVCMOS25 Standard.(1)							
T_{PSFD}/ T_{PHFD}	Full Delay (Legacy Delay or Default Delay) Global Clock Input and IFF(2) without MMCM	XC6VLX75T	1.33/ 0.03	1.44/ 0.03	1.75/ 0.03	2.18/ –0.22	ns
		XC6VLX130T	1.31/ –0.08	1.54/ –0.08	1.88/ –0.08	2.31/ –0.12	ns
		XC6VLX195T	1.36/ –0.11	1.60/ –0.11	1.97/ –0.11	2.40/ –0.25	ns
		XC6VLX240T	1.36/ –0.11	1.60/ –0.11	1.97/ –0.11	2.40/ –0.25	ns
		XC6VLX365T	1.79/ –0.28	1.87/ –0.28	2.17/ –0.28	2.48/ –0.24	ns
		XC6VLX550T	N/A	2.22/ –0.12	2.36/ –0.12	2.77/ –0.26	ns
		XC6VLX760	N/A	2.19/ –0.24	2.35/ –0.24	2.71/ –0.21	ns
		XC6VSX315T	1.75/ –0.09	1.85/ –0.09	2.06/ –0.09	2.47/ –0.24	ns
		XC6VSX475T	N/A	2.14/ –0.14	2.31/ –0.14	2.71/ –0.30	ns
		XC6VHX250T	1.93/ –0.22	2.04/ –0.22	2.25/ –0.22	N/A	ns
		XC6VHX255T	1.81/ –0.33	2.11/ –0.33	2.56/ –0.33	N/A	ns
		XC6VHX380T	1.93/ –0.11	2.04/ –0.11	2.25/ –0.11	N/A	ns
		XC6VHX565T	N/A	2.20/ –0.12	2.39/ –0.12	N/A	ns
		XQ6VLX130T	N/A	1.54/ –0.08	1.88/ –0.08	2.31/ –0.12	ns
		XQ6VLX240T	N/A	1.60/ –0.11	1.97/ –0.11	2.40/ –0.25	ns
		XQ6VLX550T	N/A	N/A	2.36/ –0.12	2.77/ –0.26	ns
		XQ6VSX315T	N/A	1.85/ –0.09	2.06/ –0.09	2.47/ –0.24	ns
		XQ6VSX475T	N/A	N/A	2.31/ –0.14	2.71/ –0.30	ns

Notes:

1. Setup and Hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the Global Clock input signal using the slowest process, highest temperature, and lowest voltage. Hold time is measured relative to the Global Clock input signal using the fastest process, lowest temperature, and highest voltage.
2. IFF = Input Flip-Flop or Latch
3. A Zero "0" Hold Time listing indicates no hold time or a negative hold time. Negative values can not be guaranteed "best-case", but if a "0" is listed, there is no positive hold time.

Clock Switching Characteristics

The parameters in this section provide the necessary values for calculating timing budgets for Virtex-6 FPGA clock transmitter and receiver data-valid windows.

Table 71: **Duty Cycle Distortion and Clock-Tree Skew**

Symbol	Description	Device	Speed Grade				Units
			-3	-2	-1	-1L	
T_{DCD_CLK}	Global Clock Tree Duty Cycle Distortion(1)	All	0.12	0.12	0.12	0.12	ns
T_{CKSKEW}	Global Clock Tree Skew(2)	XC6VLX75T	0.15	0.16	0.18	0.17	ns
		XC6VLX130T	0.25	0.26	0.29	0.28	ns
		XC6VLX195T	0.26	0.27	0.31	0.30	ns
		XC6VLX240T	0.26	0.27	0.31	0.30	ns
		XC6VLX365T	0.28	0.29	0.31	0.31	ns
		XC6VLX550T	N/A	0.50	0.54	0.54	ns
		XC6VLX760	N/A	0.51	0.56	0.56	ns
		XC6VSX315T	0.27	0.28	0.32	0.30	ns
		XC6VSX475T	N/A	0.39	0.44	0.42	ns
		XC6VHX250T	0.25	0.26	0.29	N/A	ns
		XC6VHX255T	0.35	0.37	0.41	N/A	ns
		XC6VHX380T	0.45	0.47	0.52	N/A	ns
		XC6VHX565T	N/A	0.46	0.51	N/A	ns
		XQ6VLX130T	N/A	0.26	0.29	0.28	ns
		XQ6VLX240T	N/A	0.27	0.31	0.30	ns
		XQ6VLX550T	N/A	N/A	0.54	0.54	ns
		XQ6VSX315T	N/A	0.28	0.32	0.30	ns
		XQ6VSX475T	N/A	N/A	0.44	0.42	ns
T_{DCD_BUFIO}	I/O clock tree duty cycle distortion	All	0.08	0.08	0.08	0.08	ns
$T_{BUFIOSKEW}$	I/O clock tree skew across one clock region	All	0.03	0.03	0.03	0.02	ns
$T_{BUFIOSKEW2}$	I/O clock tree skew across three clock regions	All	0.10	0.12	0.23	0.12	ns
T_{DCD_BUFR}	Regional clock tree duty cycle distortion	All	0.15	0.15	0.15	0.15	ns

Notes:

1. These parameters represent the worst-case duty cycle distortion observable at the pins of the device using LVDS output buffers. For cases where other I/O standards are used, IBIS can be used to calculate any additional duty cycle distortion that might be caused by asymmetrical rise/fall times.
2. The T_{CKSKEW} value represents the worst-case clock-tree skew observable between sequential I/O elements. Significantly less clock-tree skew exists for I/O registers that are close to each other and fed by the same or adjacent clock-tree branches. Use the Xilinx FPGA_Editor and Timing Analyzer tools to evaluate clock skew specific to your application.